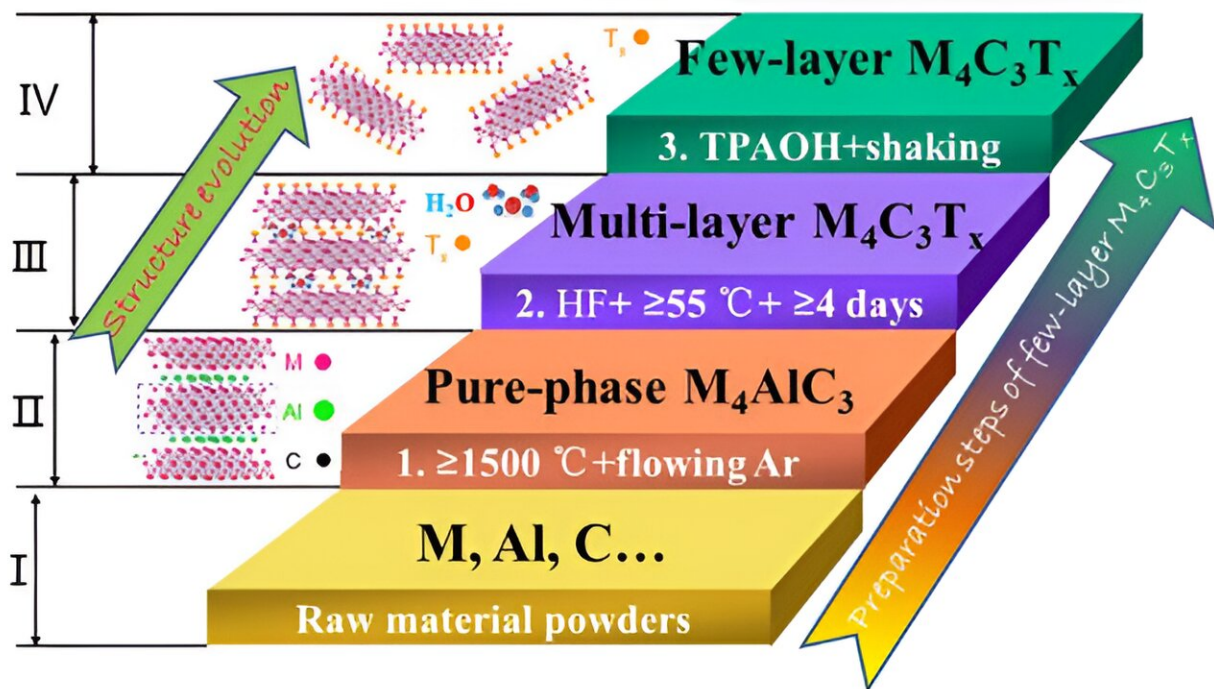


New strategy proposed for defect-free few-layer MXene nanosheets with enhanced physicochemical properties

September 4 2023, by Zhang Nannan



The preparation steps and the corresponding structure evolution of few-layer $M_4C_3T_x$ ($M = \text{V, Nb, Ta}$) MXenes. Credit: Huang Yanan

Researchers from the Hefei Institutes of Physical Science of the Chinese Academy of Sciences have proposed an optimized synthesis strategy to obtain defect-free low-layer $M_4C_3T_x$ ($M = \text{V, Nb, Ta}$) MXene

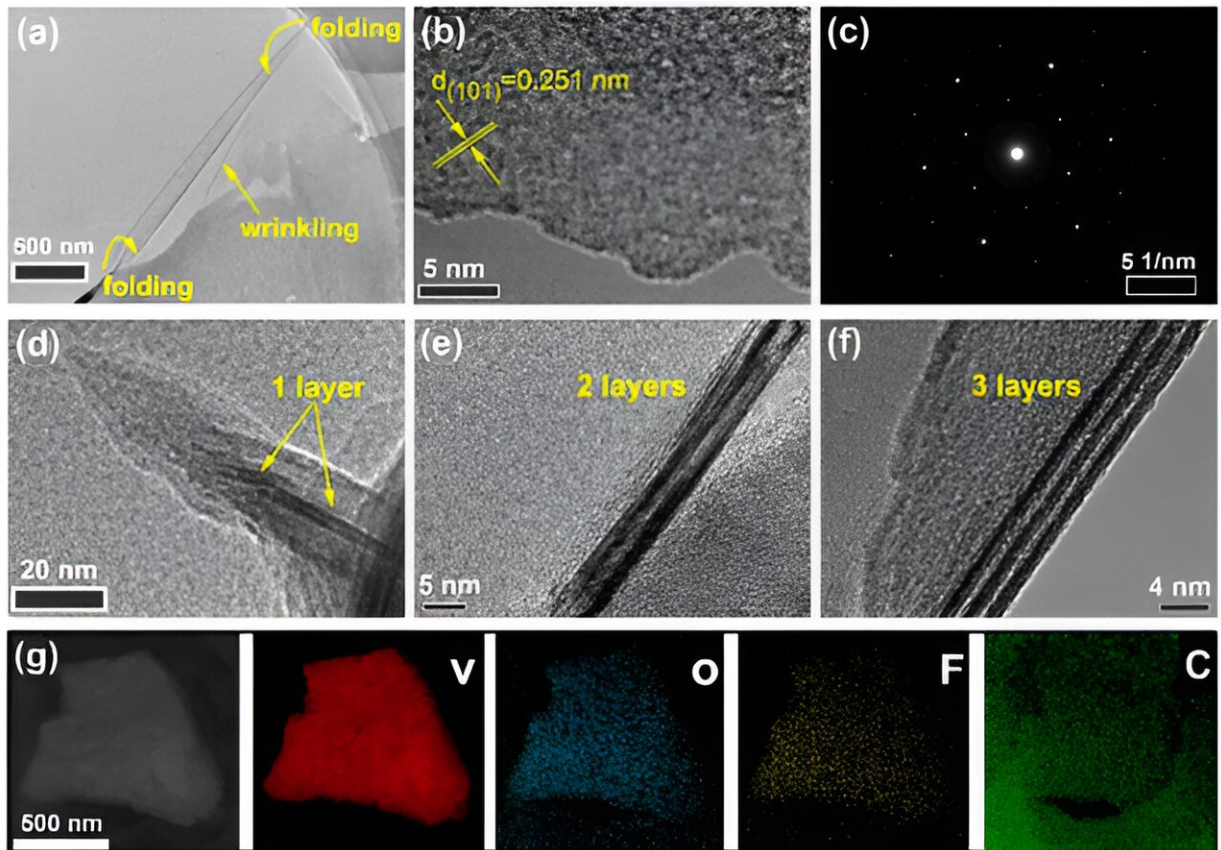
nanosheets. Their results have been published in *Advanced Science*.

MXene materials have [enormous potential](#) for applications such as [energy storage](#), energy conversion, and electromagnetic shielding due to their excellent physical and [chemical properties](#). $M_4C_3T_x$ ($M = V, Nb, Ta$) MXenes have received much attention.

However, obtaining a pure MAX phase precursor, complete etching for multi-layer $M_4C_3T_x$ MXenes, and strict requirements for intercalation agents and exfoliation operations are all difficulties in the synthesis of these few-layer $M_4C_3T_x$ MXenes. As a result, only a few investigations have focused on the study of thin $M_4C_3T_x$ ($M = V, Nb, Ta$) MXenes.

In this study, the scientists propose a roadmap for the synthesis of defect-free few-layer $M_4C_3T_x$ ($M = V, Nb, Ta$) nanosheets. It includes high-temperature calcination, HF selective etching, intercalation, and exfoliation. It produces three distinct defect-free few-layer $M_4C_3T_x$ ($M = V, Nb, Ta$) nanosheets.

Extensive characterization confirms their defect-free structure, significant interlayer spacing (ranging from 1.702 to 1.955 nm), diverse functional groups (-OH, -F, -O), and abundant valence states (M^{5+} , M^{4+} , M^{3+} , M^{2+} , M^0).



The TEM results of defect-free few-layer $V_4C_3T_x$ MXene nanosheets. Credit: Huang Yanan

In addition, they fabricated a free-standing film by vacuum filtration of a few-layer $M_4C_3T_x$ ($M = V, Nb, Ta$) MXene ink, which exhibited remarkable physicochemical properties such as high conductivity, high stability, and hydrophilicity.

"Our work provides detailed guidelines for the synthesis of other defect-free few-layer MXene nanosheets," said Huang Yanan, a member of the team, "and serves as a catalyst for the extensive exploration of functional applications of $M_4C_3T_x$ ($M = V, Nb, Ta$) MXene nanosheets in the future."

More information: Yanan Huang et al, Defect-Free Few-Layer $M_4C_3T_x$ ($M = V, Nb, Ta$) MXene Nanosheets: Synthesis, Characterization, and Physicochemical Properties, *Advanced Science* (2023). [DOI: 10.1002/advs.202302882](https://doi.org/10.1002/advs.202302882)

Provided by Chinese Academy of Sciences

Citation: New strategy proposed for defect-free few-layer MXene nanosheets with enhanced physicochemical properties (2023, September 4) retrieved 3 May 2024 from <https://phys.org/news/2023-09-strategy-defect-free-few-layer-mxene-nanosheets.html>

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